



# DCR2990M85

# **Phase Control Thyristor**

Replaces DS6385-1 DS6385-2 March 2022 (LN41623)

### **FEATURES**

- Double Side Cooling
- High Surge Capability

### **APPLICATIONS**

- Crowbar
- High Power Drives
- High Voltage Power Supplies
- Static Switches

### **VOLTAGE RATINGS**

Part and Ordering Number	Repetitive Peak Voltages VDRM and VRRM (V)	Conditions
		T <sub>vj</sub> = -40°C to 125°C,
DCR2990M85*	8500	IDRM = IRRM = 300mA,
DCR2990M80	8000	VDRM, VRRM tp = 10ms
DCR2990M75	7500	VDSM & VRSM =
DCR2990M70	7000	VDRM & VRRM + 100V
		respectively

Lower voltage grades available.

### **KEY PARAMETERS**

$\mathbf{V}_{DRM}$	8500V
IT(AV)	2990A
Ітѕм	36600A
dV/dt*	1500V/µs
dl/dt	200A/μs

<sup>\*</sup> Higher dV/dt selections are available on request

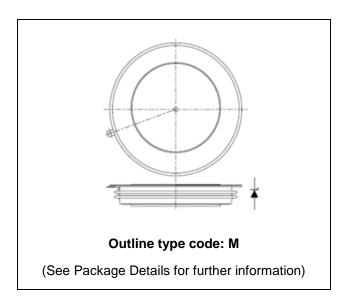


Fig. 1 Package outline

### **ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

### DCR2990M85

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

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<sup>\*8200</sup>V @ -40°C, 8500V @ 0°C



# **CURRENT RATINGS**

# T<sub>case</sub> = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
İT(AV)	Mean on-state current	Half wave resistive load	2990	А
IT(RMS)	RMS value	-	4700	Α
lτ	Continuous (direct) on-state current	-	4450	А

# **SURGE RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
Ітѕм	Surge (non-repetitive) on-state current	10ms half sine, Tcase = 125°C	36.6	kA
l²t	I2t for fusing	V <sub>R</sub> = 0	6.70	MA <sup>2</sup> s

# THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
	Double side cooled		DC	-	5.2	°C/kW
Rth(j-c)	Thermal resistance - junction to case	Cinale side seeled	Anode DC	-	10.1	°C/kW
		Single side cooled	Cathode DC	-	10.8	°C/kW
Date 15	The war of was interest and a section to	rmal resistance - case to heatsink  Clamping force 83kN (with mounting compound)	Double side	-	1.0	°C/kW
Rth(c-h)	rnermai resistance - case to neatsink		Single side	-	2.0	°C/kW
Tvj	Virtual junction temperature	Blocking VDRM / VRRM		-	125	°C
Tstg	Storage temperature range			-55	125	°C
Fm	Clamping force			74	91	kN

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# **DYNAMIC CHARACTERISTICS**

Symbol Parameter		Test Conditions		Max.	Units
1/1	Peak reverse and off-state current	At VRRM/VDRM, Tcase = 125°C	-	300	mA
IRRM/IDRM	Peak reverse and oir-state current	At 50% VRRM/VDRM, Tcase = 125°C	30	-	mA

Symbol	Parameter	Test Condition	ıs	Min.	Max.	Units
Vтм	Instantaneous forward voltage	At 4000A peak, Tj = 125°C		2.35	2.65	V
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V <sub>DRM</sub> , Tj = 125°C, g	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% VDRM to 2x IT(AV)	Repetitive 50Hz	-	100	A/µs
di/dt	Nate of fise of off-state current	Gate source 30V, $10\Omega$ tr < $0.5\mu$ s, $T_j = 125$ °C	Non-repetitive	-	200	A/µs
Varan	Threshold voltage - Low level	500A to 3000A at Tcase = 125°C		-	1.09	>
<b>V</b> т(то)	Threshold voltage - High level	h level 3000A to 9000A at Tcase = 125°C		-	1.27	V
_	On-state slope resistance - Low level	500A to 3000A at Tcase = 125°C		-	0.40	mΩ
ľτ	On-state slope resistance - High level	3000A to 9000A at Tcase = 125°C		-	0.34	mΩ
tgd	Delay time	V <sub>D</sub> = 67% V <sub>DRM</sub> , gate source tr = 0.5μs, Tj = 25°C	e 30V, 10Ω	-	3	μs
tq	Turn-off time	, ,	Iτ = 3000A, Tj = 125°C, VR = 200V, dl/dt = 1A/μs, dVpR/dt = 20V/μs linear		1000	μs
Qs	Stored charge $I_T = 2000A$ , $T_j = 125$ °C, $dI/dt = 1A/\mu s$		7240	11760	μC	
Irr	Reverse recovery current	$V_R \sim 3400V$ , $C_S = 1.5 \mu F$ , $R_S = 63 \Omega$		68	87	Α
lι	Latching current	Tj = 25°C, VD = 5V		-	3	А
Ін	Holding current	Tj = 25°C, Rg-к = ∞, Iтм = 50	0A, Ιτ = 5A	-	300	mA

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### **GATE TRIGGER CHARACTERISTICS AND RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
<b>V</b> GT	Gate trigger voltage	VDRM = 5V, Tcase = 25°C	1.5	٧
<b>V</b> GD	Gate non-trigger voltage	At 50% VDRM, Tcase = 125°C	0.4	V
Ідт	Gate trigger current	VDRM = 5V, Tcase = 25°C	400	mA
lgp	Gate non-trigger current	At 50% VDRM, Tcase = 125°C	10	mA

### **CURVES**

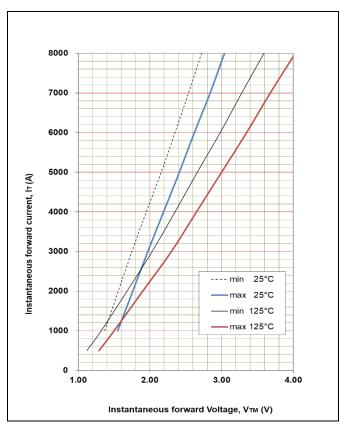


Fig. 2 Maximum & minimum on-state characteristics

# **VTM EQUATION**

 $V_{TM} = A + B.ln(I_T) + C.I_T + D.\sqrt{I_T}$ 

Where A = -0.067682

B = 0.214647

C = 0.000363

D = -0.008115

These values are valid for  $T_j = 125^{\circ}C$  for  $I_{T}$  500A to 9000A

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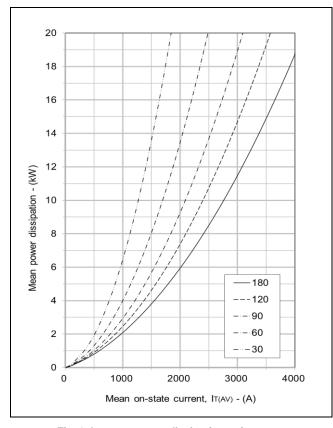


Fig. 3 On-state power dissipation - sine wave

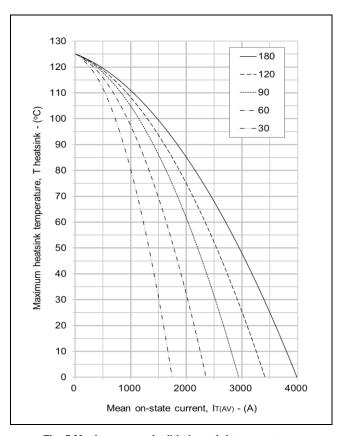


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

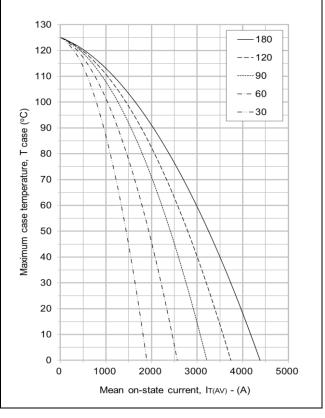


Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

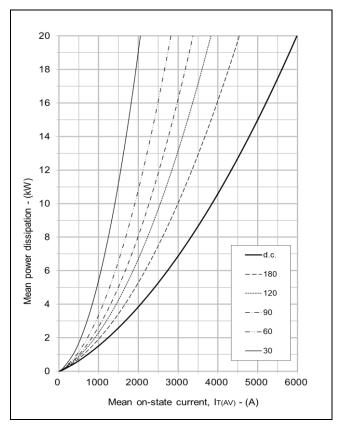


Fig. 6 On-state power dissipation - rectangular wave

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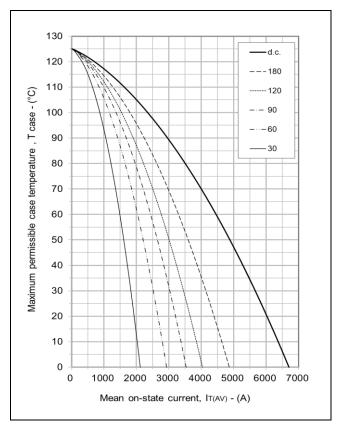
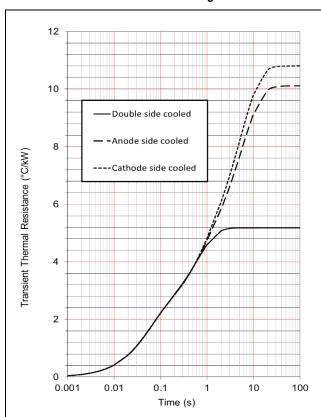


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave



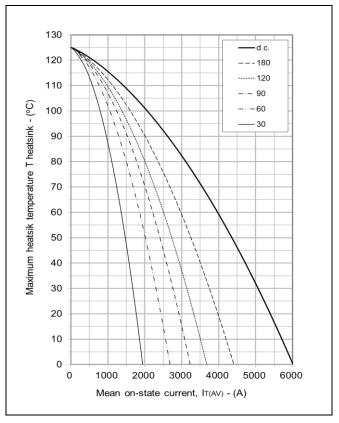


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

		1	2	3	4
Double side cooled	Ri(°C/kW)	1.995	1.243	1.945	0.005
Double side cooled	Ti(s)	0.050	0.593	0.592	110.511
Anode side cooled	Ri(°C/kW)	6.093	1.957	2.042	0.036
	Ti(s)	5.460	0.511	0.050	110.174
Cathode side	Ri(°C/kW)	6.857	1.876	2.063	0.025
cooled	Ti(s)	5.181	0.557	0.050	110.155

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

 $\Delta R_{\text{th(j-c)}}$  Conduction

Tables show the increments of thermal resistance R  $_{\text{th}(j-c)}$  when the device operates at conduction angles other than d.c.

D	Double side cooling			
	$\Delta Z_{th}$	(Z)		
θ°	sine.	rect.		
180	0.51	0.36		
120	0.57	0.49		
90	0.64	0.56		
60	0.70	0.63		
30	0.74	0.71		
15	0.76	0.74		

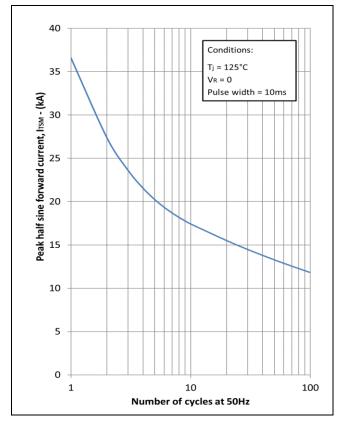
	ΑI	lode Side	lode Side Cooling		
		$\Delta Z_t$	<sub>h</sub> (Z)		
	θ°	sine.	rect.		
	180	0.51	0.36		
	120	0.58	0.50		
	90	0.65	0.57		
	60	0.71	0.64		
	30	0.75	0.71		
	15	0.77	0.75		

0 11 1 0:1 10 1:			
Cathode Sided Cooling			
	ΔZ	th (Z)	
θ°	sine.	rect.	
180	0.51	0.36	
120	0.58	0.50	
90	0.65	0.57	
60	0.71	0.64	
30	0.75	0.71	
15	0.77	0.75	

Fig.9 Maximum (limit) transient thermal impedance - junction to case (degC/kW)

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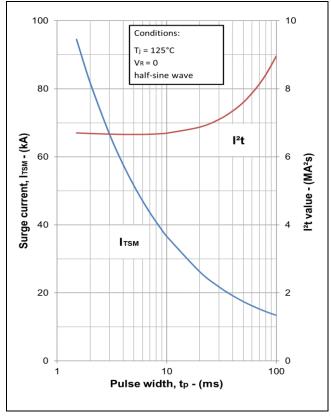


Fig. 10 Multi-cycle surge current

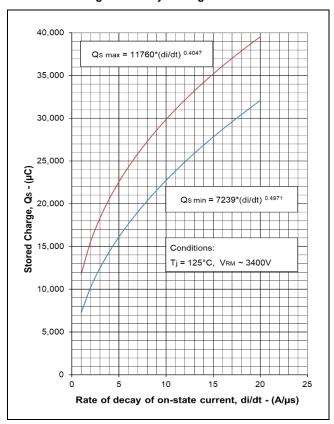


Fig. 12 Stored charge

Fig. 11 Single-cycle surge current

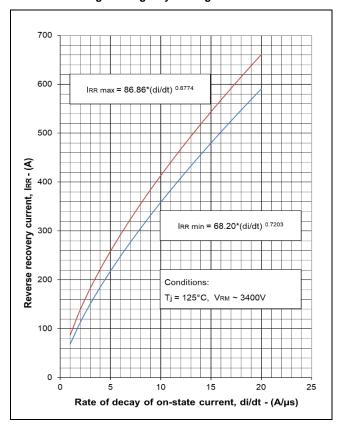


Fig. 13 Reverse recovery current

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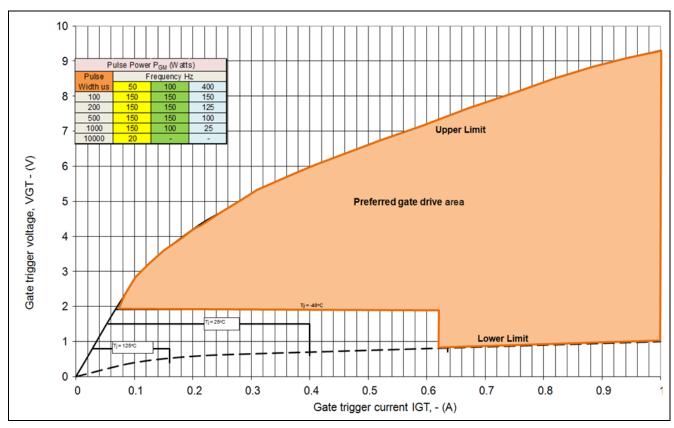


Fig.14 Gate characteristics

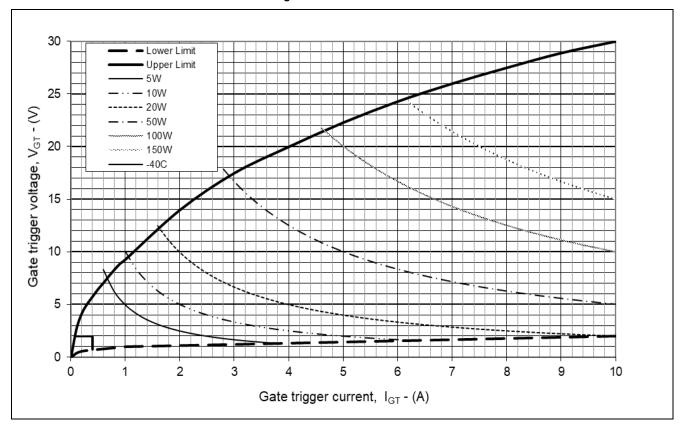


Fig. 15 Gate characteristics

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### **PACKAGE DETAILS**

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

### DO NOT SCALE

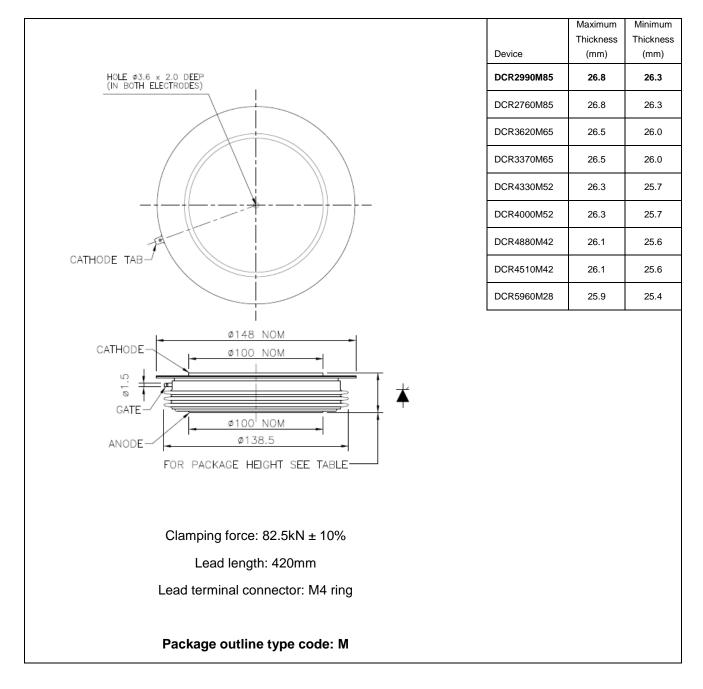


Fig. 16 Package outline

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